Francesco La Via

List of Publications by Citations

371 papers	3,786 citations	26 h-index	44 g-index
391 ext. papers	4,147 ext. citations	1.9 avg, IF	5.07 L-index

#	Paper	IF	Citations
371	Richardson constant in inhomogeneous silicon carbide Schottky contacts. *Journal of Applied Physics*, **2003**, 93, 9137-9144	2.5	201
370	Structural and electrical characterisation of titanium and nickel silicide contacts on silicon carbide. *Microelectronic Engineering*, **2002**, 60, 269-282	2.5	114
369	The NUMEN project: NUclear Matrix Elements for Neutrinoless double beta decay. *European Physical Journal A*, **2018**, 54, 1	2.5	92
368	4H SiC Epitaxial Growth with Chlorine Addition. *Chemical Vapor Deposition*, **2006**, 12, 509-515		77
367	Highly reproducible ideal SiC Schottky rectifiers: effects of surface preparation and thermal annealing on the Ni/6H-SiC barrier height. *Applied Physics A: Materials Science and Processing*, **2003**, 77, 827-833	2.6	73
366	From thin film to bulk 3C-SiC growth: Understanding the mechanism of defects reduction. *Materials Science in Semiconductor Processing*, **2018**, 78, 57-68	4.3	72
365	Schottky ohmic transition in nickel silicide/SiC-4H system: is it really a solved problem?. *Microelectronic Engineering*, **2003**, 70, 519-523	2.5	67
364	OHMIC CONTACTS TO SIC. *International Journal of High Speed Electronics and Systems*, **2005**, 15, 781-820	0.5	65
363	Structural and electrical properties of Ni Ti Schottky contacts on silicon carbide upon thermal annealing. *Journal of Applied Physics*, **2004**, 96, 4313-4318	2.5	60
362	Thin crystalline 3C-SiC layer growth through carbonization of differently oriented Si substrates. *Journal of Applied Physics*, **2007**, 102, 023518	2.5	59
361	4H-SiC epitaxial layer growth by trichlorosilane (TCS). *Journal of Crystal Growth*, **2008**, 311, 107-113	1.6	58
360	Improvement of high temperature stability of nickel contacts on n-type 6H SiC. *Applied Surface Science*, **2001**, 184, 295-298	6.7	58
359	Mechanisms of growth and defect properties of epitaxial SiC. *Applied Physics Reviews*, **2014**, 1, 031301	17.3	56
358	High performance SiC detectors for MeV ion beams generated by intense pulsed laser plasmas. *Journal of Materials Research*, **2013**, 28, 87-93	2.5	56
357	Heteroepitaxy of 3C-SiC on different on-axis oriented silicon substrates. *Journal of Applied Physics*, **2009**, 105, 084910	2.5	55
356	High-quality 6inch (111) 3C-SiC films grown on off-axis (111) Si substrates. *Thin Solid Films*, **2010**, 518, S165-S169	2.2	55
355	Effects of annealing temperature on the degree of inhomogeneity of nickel-silicide/SiC Schottky barrier. *Journal of Applied Physics*, **2005**, 98, 023713	2.5	52

354	New Achievements on CVD Based Methods for SiC Epitaxial Growth. *Materials Science Forum*, **2005**, 483-485, 67-72	0.4	46
353	Advanced Residual Stress Analysis and FEM Simulation on Heteroepitaxial 3C SiC for MEMS Application. *Journal of Microelectromechanical Systems*, **2011**, 20, 745-752	2.5	45
352	Structural defects in (100) 3C-SiC heteroepitaxy: Influence of the buffer layer morphology on generation and propagation of stacking faults and microtwins. *Diamond and Related Materials*, **2009**, 18, 1440-1449	3.5	43
351	A kinetic Monte Carlo method on super-lattices for the study of the defect formation in the growth of close packed structures. *Journal of Computational Physics*, **2007**, 227, 1075-1093	4.1	41
350	Defect Influence on Heteroepitaxial 3C-SiC Young Modulus. *Electrochemical and Solid-State Letters*, **2011**, 14, H161		33
349	Electrical characterization of ultra-shallow junctions formed by diffusion from a CoSi/sub 2/ layer. *IEEE Transactions on Electron Devices*, **1997**, 44, 526-534	2.9	30
348	3C-SiC Film Growth on Si Substrates. *ECS Transactions*, **2011**, 35, 99-116	1	28
347	Electron backscattering from stacking faults in SiC by means of ab initio quantum transport calculations. *Physical Review B*, **2012**, 85,	3.3	27
346	Defect formation and evolution in the step-flow growth of silicon carbide: A Monte Carlo study. *Journal of Crystal Growth*, **2008**, 310, 971-975	1.6	27
345	Effect of the miscut direction in (111) 3C-SiC film growth on off-axis (111)Si. *Applied Physics Letters*, **2009**, 94, 101907	3.4	26
344	Diffusion and outdiffusion of aluminium implanted into silicon. *Semiconductor Science and Technology*, **1993**, 8, 488-494	1.8	25
343	Silicon carbide detectors study for NUMEN project. *EPJ Web of Conferences*, **2016**, 117, 10006	0.3	25
342	SiCILIA-Silicon Carbide Detectors for Intense Luminosity Investigations and Applications. *Sensors*, **2018**, 18,	3.8	25
341	Ion irradiation of inhomogeneous Schottky barriers on silicon carbide. *Journal of Applied Physics*, **2005**, 97, 123502	2.5	24
340	Structural and electronic transitions in Ge2Sb2Te5 induced by ion irradiation damage. *Physical Review B*, **2016**, 94,	3.3	24
339	SiC-4H Epitaxial Layer Growth Using Trichlorosilane (TCS) as Silicon Precursor. *Materials Science Forum*, **2006**, 527-529, 179-182	0.4	23
338	Structural characterisation of titanium silicon carbide reaction. *Microelectronic Engineering*, **2001**, 55, 375-381	2.5	23
337	Genesis and evolution of extended defects: The role of evolving interface instabilities in cubic SiC. *Applied Physics Reviews*, **2020**, 7, 021402	17.3	22

336	Growth Rate Effect on 3C-SiC Film Residual Stress on (100) Si Substrates. *Materials Science Forum*, **2010**, 645-648, 143-146	0.4	21
335	Preferential oxidation of stacking faults in epitaxial off-axis (111) 3C-SiC films. *Applied Physics Letters*, **2009**, 95, 111905	3.4	21
334	Tailoring the Ti/4H-SiC Schottky barrier by ion irradiation. *Applied Physics Letters*, **2004**, 85, 6152-6154	3.4	21
333	Silicon carbide pinch rectifiers using a dual-metal Ti-Ni/sub 2/Si Schottky barrier. *IEEE Transactions on Electron Devices*, **2003**, 50, 1741-1747	2.9	21
332	Temperature dependence of the c-axis mobility in 6H-SiC Schottky diodes. *Applied Physics Letters*, **2003**, 83, 4181-4183	3.4	21
331	Low Stress Heteroepitaxial 3C-SiC Films Characterized by Microstructure Fabrication and Finite Elements Analysis. *Journal of the Electrochemical Society*, **2010**, 157, H438	3.9	20
330	Extended study of the step-bunching mechanism during the homoepitaxial growth of SiC. *Thin Solid Films*, **2010**, 518, S159-S161	2.2	20
329	Thermal stability of thin CoSi2 layers on polysilicon implanted with As, BF2, and Si. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1998**, 16, 1129		20
328	Effect of the linewidth reduction on the characteristic time spread in C49□C54 phase transition. *Applied Physics Letters*, **1998**, 73, 3863-3865	3.4	20
327	Thermal stability of cobalt silicide stripes on Si (001). *Journal of Applied Physics*, **1999**, 86, 3089-3095	2.5	20
326	Photocatalytical activity of amorphous hydrogenated TiO2 obtained by pulsed laser ablation in liquid. *Materials Science in Semiconductor Processing*, **2016**, 42, 28-31	4.3	19
325	First Principles Investigation on the Modifications of the 4H-SiC Band Structure Due to the (4,4) and (3,5) Stacking Faults. *Applied Physics Express*, **2011**, 4, 025802	2.4	19
324	Heteroepitaxial growth of (111) 3C-SiC on (110) Si substrate by second order twins. *Applied Physics Letters*, **2008**, 92, 224102	3.4	19
323	Electrical properties of high energy ion irradiated 4H-SiC Schottky diodes. *Journal of Applied Physics* , **2008**, 104, 093711	2.5	19
322	Structural properties of fluorinated SiO2 thin films. *Microelectronic Engineering*, **2000**, 50, 67-74	2.5	18
321	Nucleation and growth of C54 grains into C49 TiSi2 thin films monitored by micro-Raman imaging. *Journal of Applied Physics*, **2000**, 88, 7013-7019	2.5	18
320	Carbonization and transition layer effects on 3C-SiC film residual stress. *Journal of Crystal Growth*, **2017**, 473, 11-19	1.6	17
319	Protrusions reduction in 3C-SiC thin film on Si. *Journal of Crystal Growth*, **2018**, 498, 248-257	1.6	17

318	Fabrication of a Monolithic Implantable Neural Interface from Cubic Silicon Carbide. *Micromachines*, **2019**, 10,	3.3	17
317	Raman Characterization of Doped 3C-SiC/Si for Different Silicon Substrates and C/Si Ratios. *Materials Science Forum*, **2010**, 645-648, 255-258	0.4	17
316	Stacking faults evolution during epitaxial growths: Role of surface the kinetics. *Surface Science*, **2010**, 604, 939-942	1.8	17
315	Drift mobility in 4H-SiC Schottky diodes. *Applied Physics Letters*, **2005**, 87, 142105	3.4	17
314	Impact of Stacking Faults and Domain Boundaries on the Electronic Transport in Cubic Silicon Carbide Probed by Conductive Atomic Force Microscopy. *Advanced Electronic Materials*, **2020**, 6, 1901171	6.4	16
313	Biocompatibility between Silicon or Silicon Carbide surface and Neural Stem Cells. *Scientific Reports* , **2019**, 9, 11540	4.9	16
312	Structural and electronic characterization of (2,33) bar-shaped stacking fault in 4H-SiC epitaxial layers. *Applied Physics Letters*, **2011**, 98, 051915	3.4	16
311	Theoretical Monte Carlo Study of the Formation and Evolution of Defects in the Homoepitaxial Growth of SiC. *Materials Science Forum*, **2008**, 600-603, 135-138	0.4	16
310	Optical and electrical properties of 4H-SiC epitaxial layer grown with HCl addition. *Journal of Applied Physics*, **2007**, 102, 043523	2.5	16
309	Schottky-Ohmic Transition in Nickel Silicide/SiC System: Is it Really a Solved Problem?. *Materials Science Forum*, **2003**, 433-436, 721-724	0.4	16
308	Sublimation growth of bulk 3C-SiC using 3C-SiC-on-Si (1 0 0) seeding layers. *Journal of Crystal Growth*, **2017**, 478, 159-162	1.6	15
307	Thick Epitaxial Layers Growth by Chlorine Addition. *Materials Science Forum*, **2009**, 615-617, 55-60	0.4	15
306	Monte Carlo study of the step flow to island nucleation transition for close packed structures. *Surface Science*, **2009**, 603, 2226-2229	1.8	15
305	Two-dimensional junction profiling by selective chemical etching: Applications to electron device characterization. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1996**, 14, 414		15
304	Very High Growth Rate Epitaxy Processes with Chlorine Addition. *Materials Science Forum*, **2007**, 556-557, 157-160	0.4	15
303	High growth rate process in a SiC horizontal CVD reactor using HCl. *Microelectronic Engineering*, **2006**, 83, 48-50	2.5	15
302	Structural properties of SiO2 films prepared by plasma-enhanced chemical vapor deposition. *Materials Science in Semiconductor Processing*, **2001**, 4, 43-46	4.3	15
301	Interface state density evaluation of high quality hetero-epitaxial 3C-SiC(001) for high-power MOSFET applications. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2015**, 198, 14-19	3.1	14

300	Theoretical and experimental study of the role of cell-cell dipole interaction in dielectrophoretic devices: application to polynomial electrodes. *BioMedical Engineering OnLine*, **2014**, 13, 71	4.1	14
299	Microtwin reduction in 3C-SiC heteroepitaxy. *Applied Physics Letters*, **2010**, 97, 181916	3.4	14
298	Formation of the TiSi2 C40 as an intermediate phase during the reaction of the Si/Ta/Ti system. *Applied Physics Letters*, **2001**, 78, 1864-1866	3.4	14
297	Precipitation of arsenic diffused into silicon from a TiSi2 source. *Journal of Applied Physics*, **1991**, 69, 726-731	2.5	14
296	Stress fields analysis in 3C-SiC free-standing microstructures by micro-Raman spectroscopy. *Thin Solid Films*, **2012**, 522, 20-22	2.2	13
295	High Quality Single Crystal 3C-SiC(111) Films Grown on Si(111). *Materials Science Forum*, **2009**, 615-617, 145-148	0.4	13
294	Epitaxial Layers Grown with HCl Addition: A Comparison with the Standard Process. *Materials Science Forum*, **2006**, 527-529, 163-166	0.4	13
293	High-resolution investigation of atomic interdiffusion during Co/Ni/Si phase transition. *Journal of Applied Physics*, **2003**, 94, 231-237	2.5	13
292	Direct measurement of the growth rate during the C49 to C54 transformation in TiSi2: Activation energy. *Journal of Applied Physics*, **2002**, 92, 627-628	2.5	13
291	Roughness of thermal oxide layers grown on ion implanted silicon wafers. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1998**, 16, 619		13
290	(Invited) Three-Dimensional Epitaxial Si1-XGex, Ge and SiC Crystals on Deeply Patterned Si Substrates. *ECS Transactions*, **2014**, 64, 631-648	1	12
289	Micro-Raman analysis and finite-element modeling of 3 C-SiC microstructures. *Journal of Raman Spectroscopy*, **2013**, 44, 299-306	2.3	12
288	Patterned substrate with inverted silicon pyramids for 3C-SiC epitaxial growth: A comparison with conventional (001) Si substrate. *Journal of Materials Research*, **2013**, 28, 94-103	2.5	12
287	Investigations of transient phase formation in Ti/Si thin film reaction. *Journal of Applied Physics*, **2004**, 96, 361-368	2.5	12
286	Defect Reduction in Epitaxial 3C-SiC on Si(001) and Si(111) by Deep Substrate Patterning. *Materials Science Forum*, **2015**, 821-823, 193-196	0.4	11
285	Ion Implantation Defects in 4H-SiC DIMOSFET. *Materials Science Forum*, **2016**, 858, 418-421	0.4	11
284	Temperature Investigation on 3C-SiC Homo-Epitaxy on Four-Inch Wafers. *Materials*, **2019**, 12,	3.5	11
283	Optical investigation of bulk electron mobility in 3C-SiC films on Si substrates. *Applied Physics Letters*, **2010**, 97, 142103	3.4	11

282	Reduction of the C49-C54 TiSi 2 phase transformation temperature by reactive Ti deposition. *Europhysics Letters*, **1997**, 40, 581-586	1.6	11
281	Defect-induced tetragonalization of the orthorhombic TiSi2 C49 phase: X-ray diffraction and first principles calculations. *Applied Physics Letters*, **2001**, 78, 739-741	3.4	11
280	Electrical resistivity and Hall coefficient of C49, C40, and C54 TiSi2 thin-film phases. *Journal of Applied Physics*, **2002**, 92, 3147-3151	2.5	11
279	Role of the substrate in the C49→C54 transformation of TiSi2. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2000**, 18, 721		11
278	Arsenic redistribution at the SiO2/Si interface during oxidation of implanted silicon. *Physical Review B*, **1998**, 58, 10990-10999	3.3	11
277	Extended defects in 3C-SiC: Stacking faults, threading partial dislocations, and inverted domain boundaries. *Acta Materialia*, **2021**, 213, 116915	8.4	11
276	3C-SiC Hetero-Epitaxially Grown on Silicon Compliance Substrates and New 3C-SiC Substrates for Sustainable Wide-Band-Gap Power Devices (CHALLENGE). *Materials Science Forum*, **2018**, 924, 913-918	0.4	10
275	On the "Step Bunching" Phenomena Observed on Etched and Homoepitaxially Grown 4H Silicon Carbide. *Materials Science Forum*, **2011**, 679-680, 358-361	0.4	10
274	Complete Determination of the Local Stress Field in Epitaxial Thin Films Using Single Microstructure. *Materials Science Forum*, **2011**, 679-680, 213-216	0.4	10
273	3C-SiC Hetero-Epitaxial Films for Sensors Fabrication. *Advances in Science and Technology*, **2008**, 54, 411-415	0.4	10
272	TEM analysis of an additional metal-rich component at the C49→C54 transformation in Ti/Si thin films capped with TiN. *Thin Solid Films*, **2002**, 408, 123-127	2.2	10
271	In situ investigations of the metal/silicon reaction in Ti/Si thin films capped with TiN: Volumetric analysis of the C49→C54 transformation. *Applied Physics Letters*, **2001**, 79, 2184-2186	3.4	10
270	Thermal oxidation of Si (001) single crystal implanted with Ge ions. *Journal of Applied Physics*, **2002**, 91, 6754	2.5	10
269	Epitaxial CoSi2 formation on Si(001) from an amorphous Co75W25 sputtered layer. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1992**, 10, 2284		10
268	Ni/4H-SiC interaction and silicide formation under excimer laser annealing for ohmic contact. *Materialia*, **2020**, 9, 100528	3.2	10
267	Stacking Fault Analysis of Epitaxial 3C-SiC on Si(001) Ridges. *Materials Science Forum*, **2016**, 858, 147-150	0.4	10
266	Formation, Morphology, and Optical Properties of Electroless Deposited Gold Nanoparticles on 3C-SiC. *Journal of Physical Chemistry C*, **2017**, 121, 4304-4311	3.8	9
265	Generation and Termination of Stacking Faults by Inverted Domain Boundaries in 3C-SiC. *Crystal Growth and Design*, **2020**, 20, 3104-3111	3.5	9

264	Photo-electrochemical water splitting in silicon based photocathodes enhanced by plasmonic/catalytic nanostructures. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2017**, 225, 128-133	3.1	9
263	Reduction of the Surface Density of Single Shockley Faults by TCS Growth Process. *Materials Science Forum*, **2011**, 679-680, 67-70	0.4	9
262	Dual metal SiC Schottky rectifiers with low power dissipation. *Microelectronic Engineering*, **2003**, 70, 524-528	2.3	9
261	Activation Study of Implanted N+ in 6H-SiC by Scanning Capacitance Microscopy. *Materials Science Forum*, **2003**, 433-436, 375-378	0.4	9
260	Dopant profile measurements in ion implanted 6H□SiC by scanning capacitance microscopy. *Applied Surface Science*, **2001**, 184, 183-189	6.7	9
259	Oxidation of ion implanted silicon carbide. *Materials Science in Semiconductor Processing*, **2001**, 4, 345-349	4.3	9
258	Effects of N-induced heterogeneous nucleation and growth of cavities at the CoSi2/polycrystalline□ilicon interface. *Applied Physics Letters*, **2002**, 81, 55-57	3.4	9
257	High temperature annealing effects on the electrical characteristics of C implanted Si. *Journal of Applied Physics*, **1996**, 79, 3464-3469	2.5	9
256	The NUMEN Heavy Ion Multidetector for a Complementary Approach to the Neutrinoless Double Beta Decay. *Universe*, **2020**, 6, 129	2.5	9
255	3C-SiC Epitaxy on Deeply Patterned Si(111) Substrates. *Materials Science Forum*, **2016**, 858, 151-154	0.4	9
254	New thick silicon carbide detectors: Response to 14 MeV neutrons and comparison with single-crystal diamonds. *Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment*, **2019**, 946, 162637	1.2	8
253	3C-SiC grown on Si by using a Si1-xGex buffer layer. *Journal of Crystal Growth*, **2019**, 519, 1-6	1.6	8
252	Evaluation of 3C-SiC/Si residual stress and curvatures along different wafer direction. *Materials Letters*, **2014**, 118, 130-133	3.3	8
251	A novel micro-Raman technique to detect and characterize 4H-SiC stacking faults. *Journal of Applied Physics*, **2014**, 116, 163506	2.5	8
250	Study of the Effects of Growth Rate, Miscut Direction and Postgrowth Argon Annealing on the Surface Morphology of Homoepitaxially Grown 4H Silicon Carbide Films. *Materials Science Forum*, **2013**, 740-742, 229-234	0.4	8
249	Study of the connection between stacking faults evolution and step kinetics in misoriented 4H-SiC epitaxial growths. *Surface Science*, **2011**, 605, L67-L69	1.8	8
248	Study of the Evolution of Basal Plane Dislocations during Epitaxial Growth: Role of the Surface Kinetics. *Materials Science Forum*, **2010**, 645-648, 539-542	0.4	8
247	3C-SiC Heteroepitaxial Growth on Inverted Silicon Pyramids (ISP). *Materials Science Forum*, **2010**, 645-648, 135-138	0.4	8

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245	SiC Films and Coatings **2012**, 17-61		8
244	SiC-4H Epitaxial Layer Growth by Trichlorosilane (TCS) as Silicon Precursor at Very High Growth Rate. *Materials Science Forum*, **2008**, 600-603, 123-126	0.4	8
243	Correlation between microstructure control, density and diffusion barrier properties of TiN(O) films. *Microelectronic Engineering*, **2002**, 60, 81-87	2.5	8
242	Thermal expansion and stress development in the first stages of silicidation in Ti/Si thin films. *Journal of Applied Physics*, **2003**, 94, 7083-7090	2.5	8
241	Improvement of CoSi2 thermal stability by cavity formation. *Applied Physics Letters*, **2001**, 79, 3419-3421	3.4	8
240	Reaction of the Si/Ta/Ti system: C40 TiSi2 phase formation and in situ kinetics. *Journal of Applied Physics*, **2002**, 91, 633-638	2.5	8
239	Precipitation of As in thermally oxidized ion-implanted Si crystals. *Applied Physics Letters*, **1998**, 73, 2633-2635	3.4	8
238	Arsenic and boron diffusion in silicon from implanted cobalt silicide layers. *Semiconductor Science and Technology*, **1995**, 10, 1362-1367	1.8	8
237	Titanium silicide as a diffusion source for phosphorous: precipitation and activation. *Applied Surface Science*, **1991**, 53, 190-195	6.7	8
236	An energy dispersion spectroscopy technique to measure titanium silicide lateral diffusion. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1989**, 7, 2609-2613	2.9	8
235	3C-SiC Growth on Inverted Silicon Pyramids Patterned Substrate. *Materials*, **2019**, 12,	3.5	8
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233	Nuclear fragment identification with ΔE-E telescopes exploiting silicon carbide detectors. *Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment*, **2019**, 925, 60-69	1.2	7
232	Growth of Large-Area, Stress-Free, and Bulk-Like 3C-SiC (100) Using 3C-SiC-on-Si in Vapor Phase Growth. *Materials*, **2019**, 12,	3.5	7
231	Laser Annealing of P and Al Implanted 4H-SiC Epitaxial Layers. *Materials*, **2019**, 12,	3.5	7
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229	Study of microstructure deflections and film/substrate curvature under generalized stress fields and mechanical properties. *Thin Solid Films*, **2012**, 522, 26-29	2.2	7

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227	Raman Stress Characterization of Hetero-Epitaxial 3C-SiC Free Standing Structures. *Materials Science Forum*, **2011**, 679-680, 141-144	0.4	7
226	Kinetics of the C49C54 phase transition in TiSi2: New indications from sheet resistance, infrared spectroscopy and molecular dynamics simulations. *Microelectronic Engineering*, **1997**, 37-38, 441-448	2.5	7
225	Environment influence on Ti diffusion and layer degradation of a SiC/Ni2Si/TiW/Au contact structure. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2004**, 22, 966		7
224	Thermal oxidation of As and Ge implanted Si(). *Surface Science*, **2003**, 532-535, 746-753	1.8	7
223	Structural relationship of polycrystalline cobalt silicide lines to (001) silicon substrate and their thermal stability. *Microelectronic Engineering*, **2001**, 55, 163-169	2.5	7
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220	Investigation of C49C54 TiSi2 transformation kinetics. *Microelectronic Engineering*, **2000**, 50, 153-158	2.5	7
219	Reaction and thermal stability of cobalt disilicide on polysilicon resulting from a Si/Ti/Co multilayer system. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1999**, 17, 1448		7
218	Two-Dimensional Aluminum Diffusion in Silicon: Experimental Results and Simulations. *Journal of the Electrochemical Society*, **1995**, 142, 1585-1590	3.9	7
217	Structure and defect characterization of epitaxial CoSi2 on Si(001) formed using an amorphous Co75W25 sputtered layer. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1993**, 11, 1807		7
216	Dependence of PtSi Schottky diode electrical behaviour on the platinum film thickness and on the annealing process. *Thin Solid Films*, **1988**, 161, 13-20	2.2	7
215	Silicon Carbide and MRI: Towards Developing a MRI Safe Neural Interface. *Micromachines*, **2021**, 12,	3.3	7
214	Electrical properties of extended defects in 4H-SiC investigated by photoinduced current measurements. *Applied Physics Express*, **2017**, 10, 036601	2.4	6
213	Characterization of 4H- and 6H-Like Stacking Faults in Cross Section of 3C-SiC Epitaxial Layer by Room-Temperature Photoluminescence and Raman Analysis. *Materials*, **2020**, 13,	3.5	6
212	Micro-Raman Characterization of 4H-SiC Stacking Faults. *Materials Science Forum*, **2014**, 778-780, 378-381	0.4	6
211	Detection of Crystallographic Defects in 3C-SiC by Micro-Raman and Micro-PL Analysis. *Materials Science Forum*, **2017**, 897, 303-306	0.4	6

210	Analysis on 3C-SiC Layer Grown on Pseudomorphic-Si/Si1-xGex/Si(001) Heterostructures. *Materials Science Forum*, **2014**, 806, 21-25	0.4	6
209	Stress nature investigation on heteroepitaxial 3C-SiC film on (100) Si substrates. *Journal of Materials Research*, **2013**, 28, 129-135	2.5	6
208	Atomistic and Continuum Simulations of the Homo-Epitaxial Growth of SiC. *Materials Science Forum* , **2009**, 615-617, 73-76	0.4	6
207	Advanced Stress Analysis by Micro-Structures Realization on High Quality Hetero-Epitaxial 3C-SiC for MEMS Application. *Materials Science Forum*, **2011**, 679-680, 133-136	0.4	6
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